IN THE SPECIFICIATION:

Amend the title as follows:

~~**TRANSITION METAL DIELECTRIC ALLOY MATERIALS FOR MEMS**~~

MICROMECHANICAL DEVICE COMPRISING TRANSITION METAL DIELECTRIC ALLOY MATERIALS

Amend the the paragraph beginning on line 32, page 5, as follows:

A MEMS device and process showing a circuit substrate and a pull-in ~~electrode~~ electrode is illustrated in Figs. 2A to 2G. A As can be seen in Fig. 2A, a circuit (e.g CMOS) substrate 40 is provided having a patterned final metal layer 41a, 41b from the circuit process. Deposited thereon as can be seen in Fig. 2B, is a sacrificial layer 42, which can be any suitable sacrificial material as mentioned above. In the present example, the sacrificial material is amorphous silicon deposited by pressure enhanced chemical vapor deposition (PECVD) or sputtering (physical vapor deposition of PVD). The amorphous silicon can be annealed to increase stability and patterned to form apertures for MEMS structural material. Then, as can be further seen in Fig. 2B, a plug layer 43 (for example, a refractory metal such as W, Mo, Ti or Ta or a conductive metal compound) is deposited such as in a cold wall, low pressure CVD system, and preferably from a WF6 source (if the metal is W). This metal deposition is followed by chemical mechanical polishing (CMP) to form a plug 44 and a sacrificial layer 42 having a smooth surface 45

IN THE DRAWINGS:

In Figure 1I, the patterned aperture was inadvertently left out of this figure, and has been added. A corrected drawing is enclosed herewith.